



PATENT
740756-1961

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Shunpei YAMAZAKI et al.

Application No.: 09/295,607

Filed: April 22, 1999

For: SEMICONDUCTOR DEVICE HAVING
ALUMINUM NITRIDE FILM

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) Art Unit: 2811
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) Examiner: Steven LOKE
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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

May 13, 2002

Dear Sir:

In response to the Examiner's non-Final Office Action mailed February 13, 2002, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please amend claims 15-17, 27, 31, 34, 35, 39, 43-53, 55 and 58 to read as follows:

G1 15. (Amended) The device of claim 6 wherein said substrate is a glass substrate.

G2 16. (Amended) The device of claim 7 wherein said substrate is a glass substrate.

17. (Amended) The device of claim 8 wherein said substrate is a glass substrate.

G3 27. (Amended) The display of claim 21 wherein said substrate is a glass substrate.

G4 31. (Amended) The device of claim 2 wherein said aluminum nitride insulating film

has a thickness of 100 Å to 5000 Å.

33. (Amended) The device of claim 6 wherein said aluminum nitride insulating film

has a thickness of 100 Å to 5000 Å.